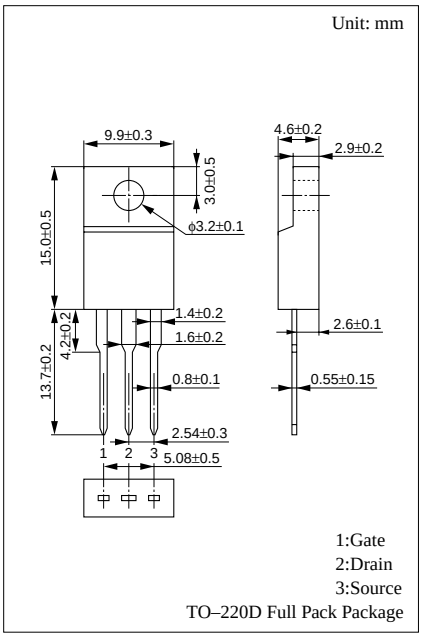
2SD2549

Silicon NPN triple diffusion planar type

For power amplification



Features

- High forward current transfer ratio h_{FE} which has satisfactory linearity
- Low collector to emitter saturation voltage $V_{CE(sat)}$
- Full-pack package which can be installed to the heat sink with one screw

Absolute Maximum Ratings (T_C=25˚C)

Parameter		Symbol	Ratings	Unit
Collector to base voltage		V_{CBO}	80	V
Collector to emitter voltage		V_{CEO}	80	V
Emitter to base voltage		V_{EBO}	6	V
Peak collector current		I_{CP}	5	A
Collector current		I_C	3	A
Collector power dissipation	T_C=25°C	P_C	20	W
	Ta=25°C		2	
Junction temperature		T_j	150	˚C
Storage temperature		T_{stg}	–55 to +150	˚C

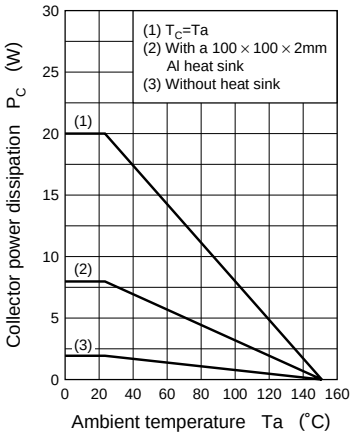
Electrical Characteristics (T_C=25˚C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CES}	V_{CE} = 70V, V_{BE} = 0			100	μA
	I_{CEO}	V_{CE} = 70V, I_B = 0			100	μA
Emitter cutoff current	I_{EBO}	V_{EB} = 6V, I_C = 0			1	mA
Collector to emitter voltage	V_{CEO}	I_C = 30mA, I_B = 0	80			V
Forward current transfer ratio	h_{FE1}*	V_{CE} = 4V, I_C = 1A	70		250	
	h_{FE2}	V_{CE} = 4V, I_C = 3A	10			
Base to emitter voltage	V_{BE}	V_{CE} = 4V, I_C = 3A			1.8	V
Collector to emitter saturation voltage	$V_{CE(sat)}$	I_C = 3A, I_B = 0.375A			0.7	V
Transition frequency	f_T	V_{CE} = 10V, I_C = 0.5A, f = 10MHz		30		MHz
Turn-on time	t_{on}	I_C = 1A, I_{B1} = 0.1A, I_{B2} = – 0.1A, V_{CC} = 50V			0.5	μs
Storage time	t_{stg}				4.5	μs
Fall time	t_f				0.5	μs

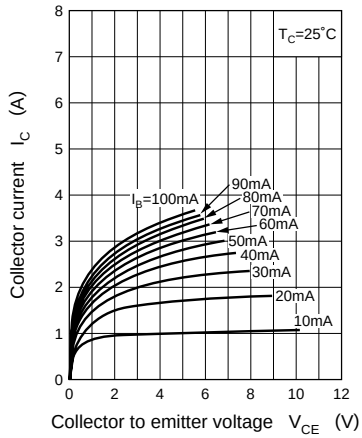
*h_{FE1} Rank classification

Rank	Q	P
h_{FE1}	70 to 150	120 to 250

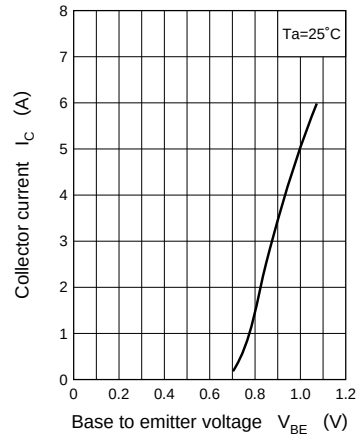
P_C — Ta



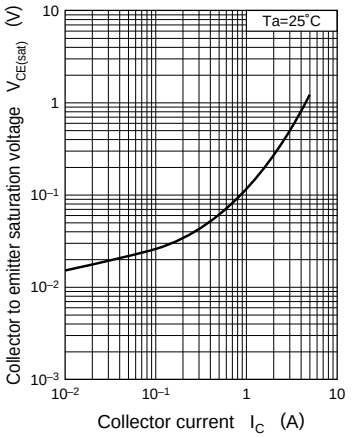
I_C — V_{CE}



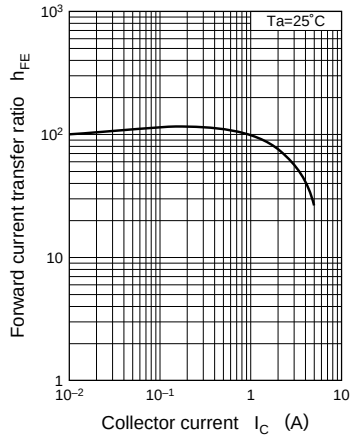
I_C — V_{BE}



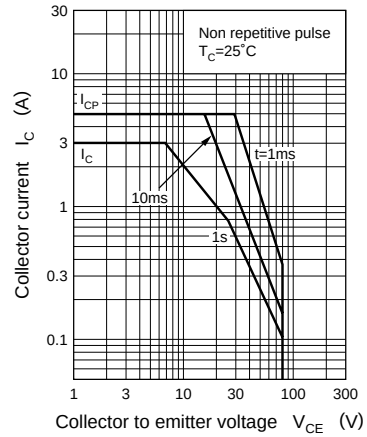
$V_{CE(sat)}$ — I_C



h_{FE} — I_C



Area of safe operation (ASO)



$R_{th(t)}$ — t